(Withdrawn) 1. A method for preparing a photoresist layer for e-beam inspection comprising:

out-gassing said photoresist layer whereby an outgas from said photoresist layer during said e-beam inspection is substantially prevented.

(Withdrawn) 2. The method for of claim 1 wherein:

said step of out-gassing said photoresist layer further comprising a step of implanting ions into said photoresist layer to activate an out-gassing from said photoresist layer.

(Withdrawn) 3. A method for preparing a photoresist layer for e-beam inspection comprising:

increasing a conductivity of said photoresist layer whereby electric charging of said photoresist layer during said e-beam inspection is substantially prevented.

(Withdrawn) 4. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting conductive ions into said photoresist layer to increase a conductivity of said photoresist layer.

(Withdrawn) 5. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting carbon ions into said photoresist layer.

(Withdrawn) 6. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting indium ions into said photoresist layer.

(Withdrawn) 7. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting Sb ions into said photoresist layer.

(Withdrawn) 8. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting silicon ions into said photoresist layer.

(Withdrawn) 9. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting metallic ions into said photoresist layer.

(Withdrawn) 10. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting a conductive ions at an implanting energy approximately 1000 ev into said photoresist layer.

(Withdrawn) 11. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of implanting a conductive ions having an ion dosage in a approximate range 10^{16} /cm^2 to 10^{18} /cm^2 into said photoresist layer.

(Withdrawn) 12. The method for of claim 3 wherein:

said step of increasing a conductivity of said photoresist layer further comprising a step of plasma immersing ion implant a conductive ions into said photoresist layer.

(Withdrawn) 13. The method for of claim 3 further comprising:

out-gassing said photoresist layer whereby an outgas from said photoresist layer during said e-beam inspection is substantially prevented.

(Withdrawn) 14. The method for of claim 13 wherein:

said step of out-gassing said photoresist layer further comprising a step of implanting ions into said photoresist layer to activate an out-gassing from said photoresist layer.

(Currently Amended) 15. A scanning electronic microscope (SEM) system for scanning a photoresist layer disposed on a semiconductor substrate for integrated circuit manufacture ~~processed for e-beam inspection~~ comprising:

a SEM disposed above said photoresist layer for projecting a scanning electronic beam (e-beam) thereto wherein said photoresist layer having an out-gas content less than 0.5 percents thus substantially prevent out-gassing from said photoresist layer during said SEM projecting said e-beam onto said photoresist layer ~~inspection~~.

(Currently Amended) 16. A scanning electronic microscope (SEM) system for scanning a photoresist layer disposed on a semiconductor substrate for integrated circuit manufacture ~~processed for e-beam inspection~~ comprising:

a SEM disposed above said photoresist layer for projecting a scanning electronic beam (e-beam) thereto wherein said photoresist layer having an electric resistivity less than 2000 ohm/cm^2 thus substantially prevent an electric charging of said photoresist layer during said SEM projecting said e-beam onto said photoresist layer ~~inspection~~.

(Currently Amended) 17. A scanning electronic microscope (SEM) system for scanning a photoresist layer disposed on a semiconductor substrate for integrated circuit manufacture comprising:

a SEM disposed above said photoresist layer for projecting a scanning electronic beam (e-beam) thereto wherein said photoresist layer having implanted conductive ions for increasing a conductivity of said photoresist layer.

(Currently Amended) 18. The scanning electronic microscope (SEM) system for scanning a photoresist layer for of claim 17 wherein:

said implanted conductive ions further comprising implanted carbon ions.

(Withdrawn) 19. The photoresist layer for of claim 17 wherein:

said implanted conductive ions further comprising implanted indium ions.

(Withdrawn) 20. The photoresist layer for of claim 17 wherein:

said implanted conductive ions further comprising implanted Sb ions.

(Withdrawn) 21. The photoresist layer for of claim 17 wherein:

said implanted conductive ions further comprising implanted silicon ions.

(Withdrawn) 22. The photoresist layer for of claim 17 wherein:

said implanted conductive ions further comprising implanted metallic ions.